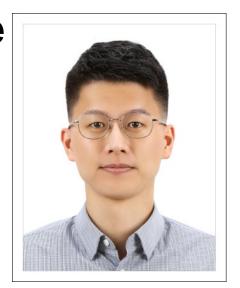
# A 16Gb 27Gb/s/pin T-coil based GDDR6 DRAM with Merged-MUX TX, Optimized WCK Operation, and Alternative-Data-Bus

<u>Daewoong Lee</u>, Hye-Jung Kwon, Daehyun Kwon, Jaehyeok Baek, Chulhee Cho, Sanghoon Kim, Donggun An, Chulsoon Chang, Unhak Lim, Jiyeon Im, Wonju Sung, Hye-Ran Kim, Sun-Young Park, HyoungJoo Kim, Hoseok Seol, Juhwan Kim, Jungbum Shin, Kil-Young Kang, Yong-Hun Kim, Sooyoung Kim, Wansoo Park, Seok-Jung Kim, Chanyong Lee, Seungseob Lee, TaeHoon Park, ChiSung Oh, Hyodong Ban, Hyungjong Ko, Hoyoung Song, Tae-Young Oh, SangJoon Hwang, Kyung Suk Oh, JungHwan Choi, Jooyoung Lee

Samsung Electronics, Korea

## **Self Introduction**

- First author (speaker): Daewoong Lee
- Education
  - B.S. in EE from KAIST, Korea in 2013
  - M.S. in EE from KAIST, Korea in 2015
  - Ph.D. in EE from KAIST, Korea in 2019



- Working at Samsung Electronics (2019.09 ~)
- **■** Interest
  - High-speed wireline interfaces
  - High-performance DRAM

## **Outline**

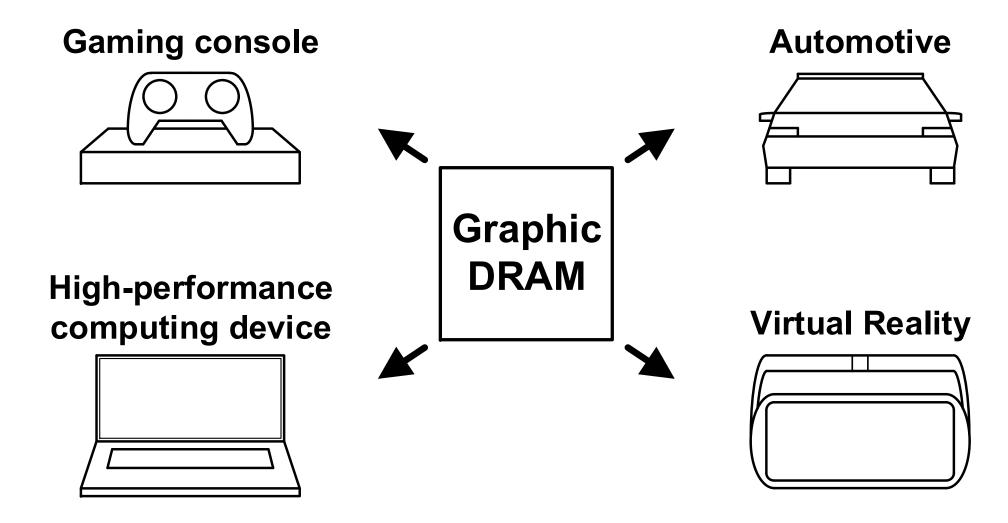
- **■** Introduction of GDDR6
- Key schemes
  - T-coil based GDDR6
  - Merged-MUX transmitter
  - WCK optimization
  - ZQ calibration
  - Alternative data bus
- Implementation and measurements
- **■** Conclusion

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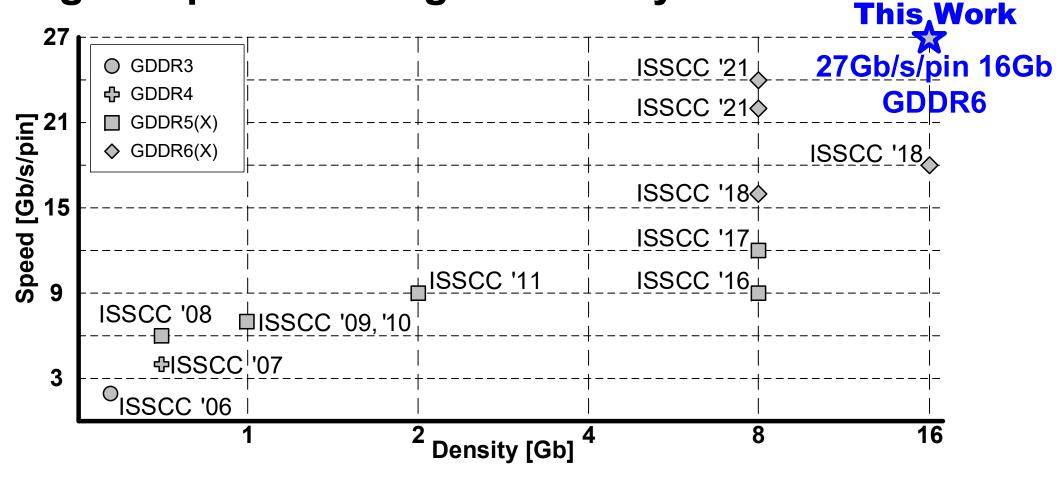
# **GDDR** application

Higher speed and higher density



## **GDDR** trend

Higher speed and higher density



→ Achieves 27Gb/s/pin by improving IO & data bus (How?)

#### **Outline**

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- T-coil based GDDR6
  - T-coil design in DRAM process
- Merged-MUX transmitter
  - Improve ISI & PSIJ
- WCK optimization
  - Quad-skew adjustment & wide freq. operation
- **■** ZQ calibration
  - T-coil impact consideration
- Alternative data bus
  - Increase data window of G-BUS by x2

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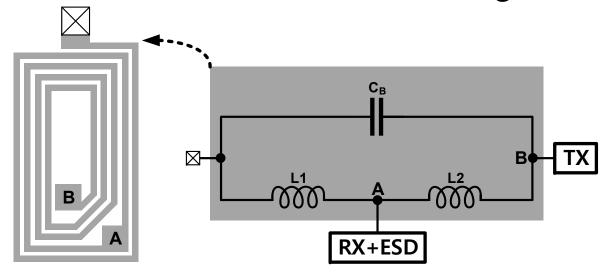
#### T-coil based GDDR6

\*Rs: Sheet resistance

\*\*RDL: Redistribution layer

- T-coil enhances I/O BW consuming no power
  - Only a few metal layers in DRAM process
    - \*Rs of \*\*RDL: 0.1 X Rs of nearest lower layer

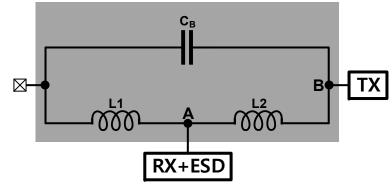
- T-coil design: RDL based T-coil layer (single layer)
  - Optimum thickness & width for T-coil design are supported



## T-coil based GDDR6

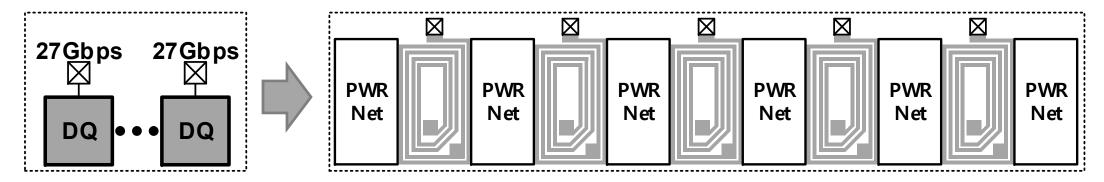
#### ■ To improve BW of both RX and TX

- Considering C<sub>TX</sub>, C<sub>ESD</sub>+C<sub>RX</sub>
  - Inductance (RDL length): L1 < L2</li>
     → Asymmetric T-coil



#### Area efficient T-coil design

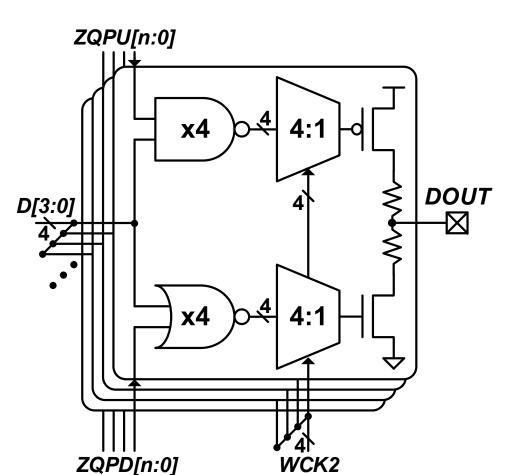
Rectangular aspect ratio, rather than square for power net



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# ZQ-coded transmitter [ISSCC'18]

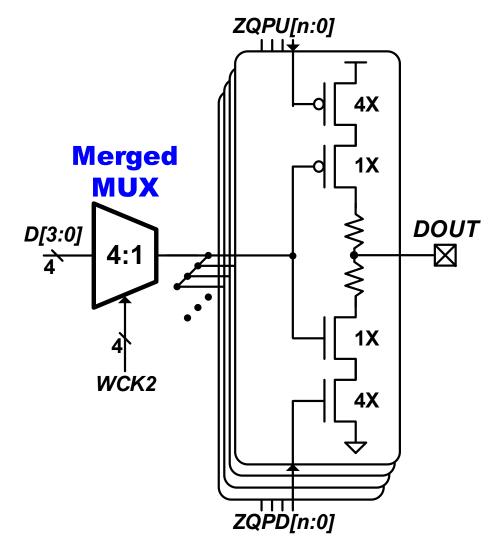
- Full-rate path: 2 stages (4:1+Out drv.)
  - → ISI & PSIJ improvement ©



- Scattered 4:1 MUXs
  - ✓ WCK2 metal loading ⊗
- Skew among multiple 4:1 MUXs
  - ✓ Degraded SI of *DOUT* ⊗
- ZQ code logic gates (NOR/NAND)
  - ✓ Power & area ⊗

# **Proposed Merged-MUX transmitter**

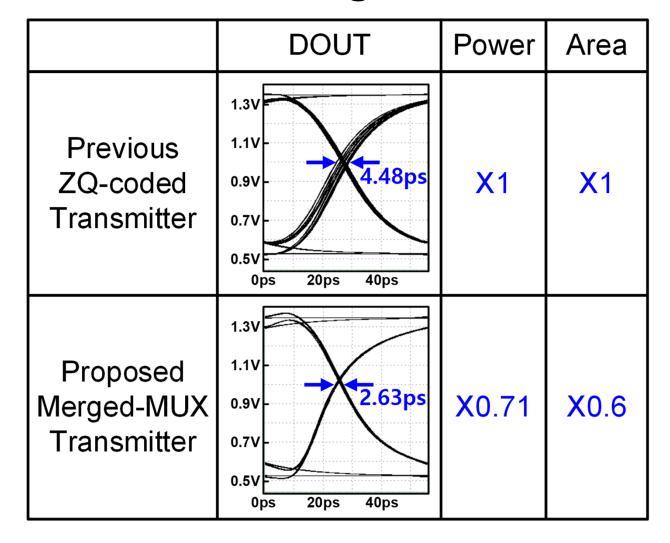
■ Full-rate path: 2 stages (4:1+Out drv.)



- Merged 4:1 MUX
  - ✓ WCK2 metal loading ②
- No skew by merged 4:1 MUX
  - ✓ Improved SI of DOUT
- No ZQ code logic gate
  - ✓ Power & area ☺

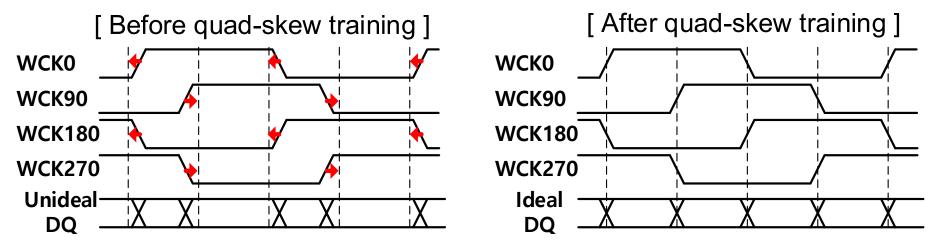
# **Transmitter comparison**

Better performance on Merged-MUX transmitter

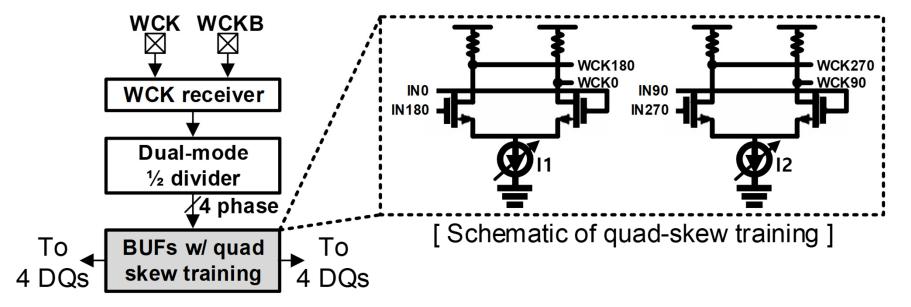


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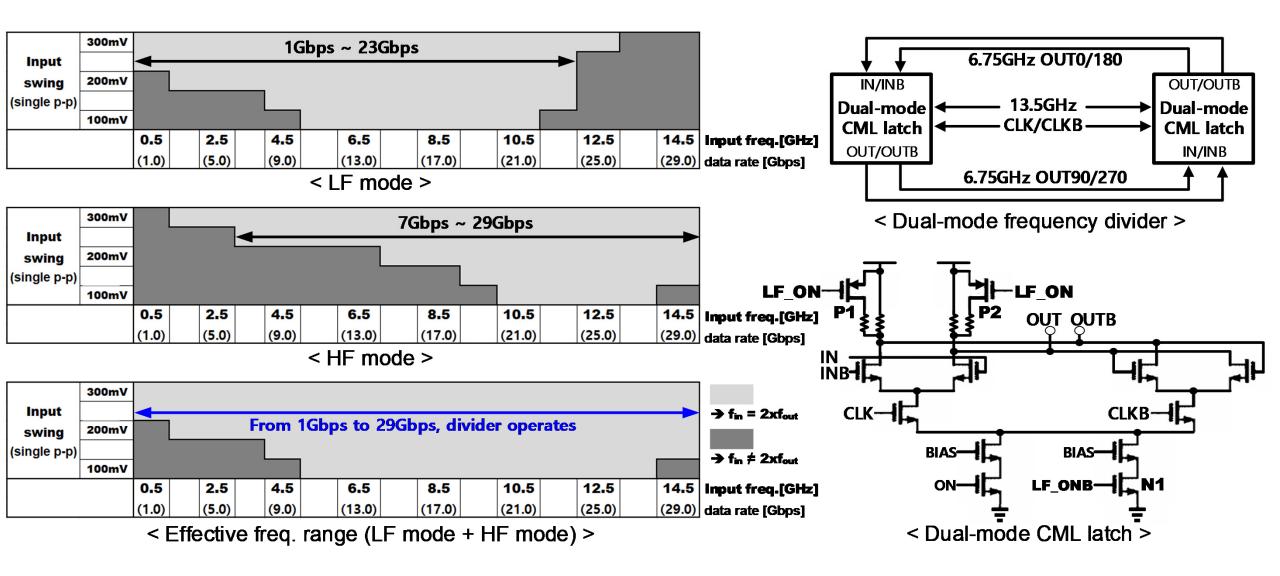
# **Quad-skew training**



Controllable max T<sub>qskew</sub>: 3ps (8.1% of 1UI for 27Gbps)



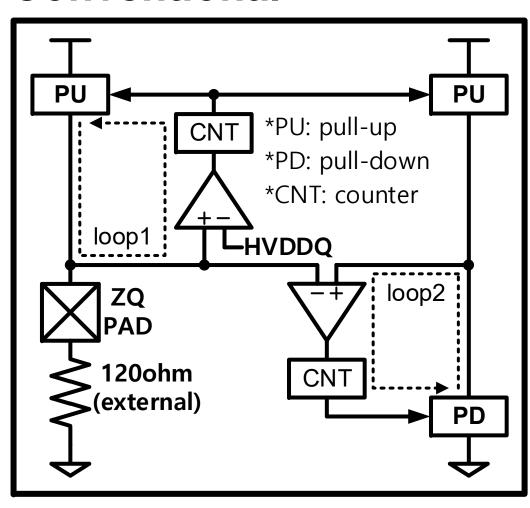
# Dual-mode frequency divider



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## **ZQ** calibration

#### Conventional



#### ●Loop1

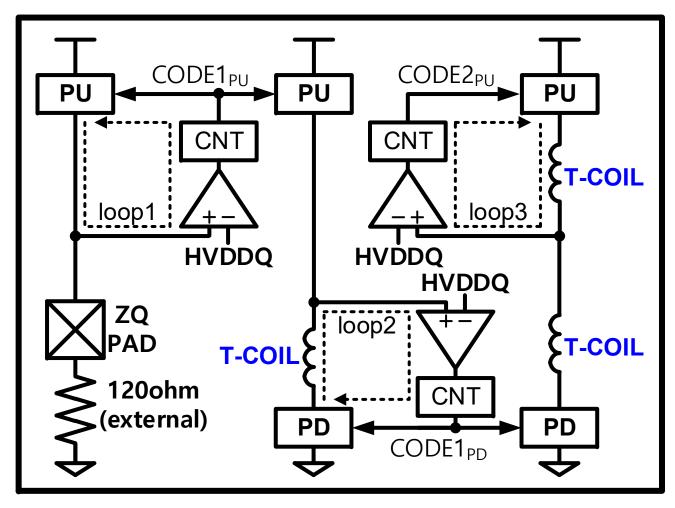
✓ Obtain pull-up codes

#### ●Loop2

✓ Obtain pull-down codes

# ZQ calibration considering T-coil

Three T-coils in calibration



#### ●Loop1

✓ Obtain pull-up codes

#### ●Loop2

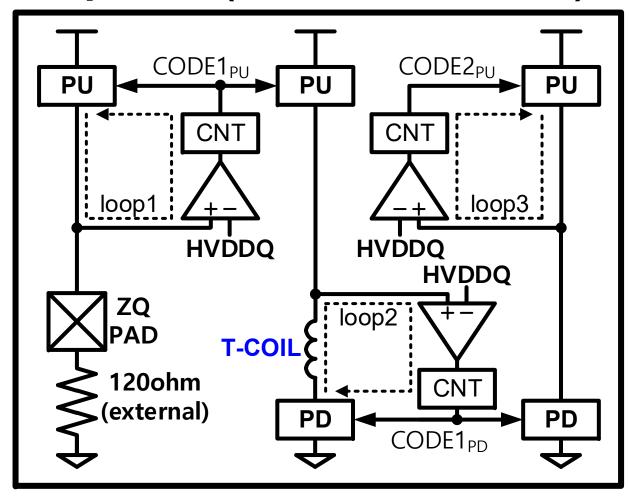
✓ Obtain pull-down codes considering T-coil

#### ●Loop3

✓ Obtain pull-up codes considering T-coil

# ZQ calibration considering T-coil

Proposed (One T-coil in cal.): area reduction

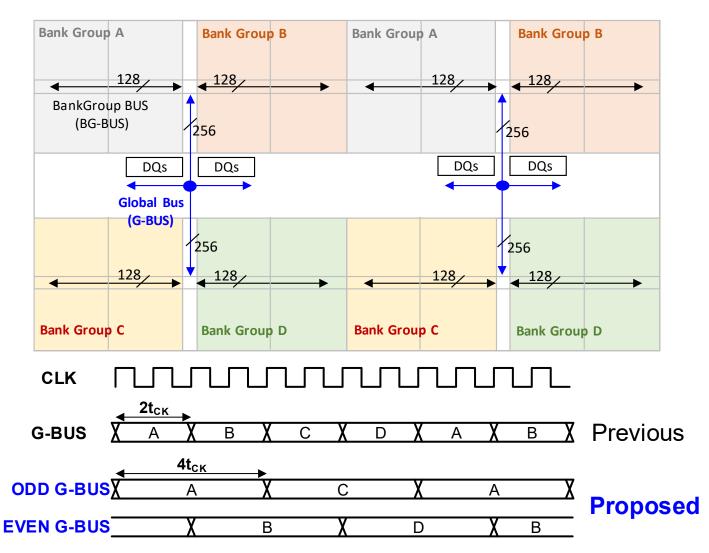


- ●Loop1
  - ✓ Obtain pull-up codes

- ●Loop2
  - ✓ Obtain pull-down codes considering T-coil
- ●Loop3
  - ✓ Obtain pull-up codes considering T-coil

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## Alternative data bus

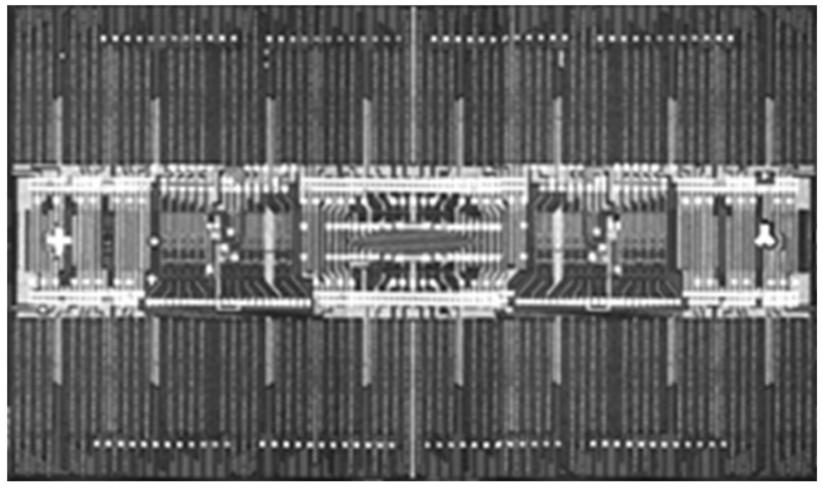


- G-bus: frequency limit
- Two G-BUSes
  - ✓ EVEN&ODD
- Increase data window of G-BUS by 2x
  - ✓ Achieve high BW (27Gbps)

## **Outline**

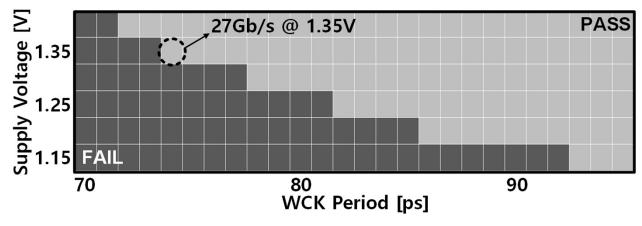
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# Chip implementation

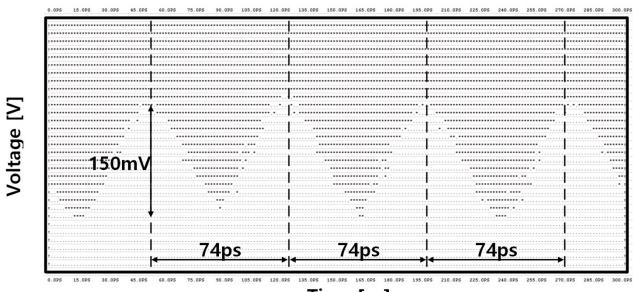


27Gb/s/pin
1z nm CMOS
Supply voltage: 1.35V
16 Bank/1-CH
8 Gb/1-CH
X16 IO/1-CH
36.3mm <sup>2</sup> /1-CH

#### Measurements



- PASS Frequency-voltage shmoo
  - ✓ 27Gb/s @ 1.35V



- Error detection code (EDC) pin
  - √ 27Gb/s (1UI=37ps)
  - √ 0101 pattern, 1.35V

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## Conclusion

■ 27Gb/s/pin 16Gb GDDR6 DRAM is implemented

#### ■ I/O Bandwidth improvement

- T-coil for the first time in DRAM process
- Merged-MUX transmitter
- Quad-skew training & dual-mode divider

#### Alternative data bus

Increase data window of G-BUS by x2